High Speed 16T Full Adder Design using 28nm CMOS Technology

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Abstract—This design has an objective to implement a full adder using transmission gate logic, in 28nm technology. Contrary to the conventional adder designs, this design has XOR/XNOR nodes which improve the circuit to operate with lesser delay. The model provides full swing even at smaller operating voltages by minimizing threshold loss observed in circuits with low supply voltages, specifically when the feature size is 28nm or less. By implementing Transmission Gate Logic, the circuit results in reduced leakage power. The circuit is to be simulated using Synopsys tools for synthesis.

I. REFERENCE CIRCUIT DETAILS

With ever-increasing computing needs and their high-speed requirements, demanding low power consumption, it becomes crucial to not only make more functional circuits but to optimize them. A key circuit in realizing arithmetic functions and address generation, is the Full Adder circuit. A common 1-bit full adder has three inputs – two binary digits and a carry-in digit, which produce two outputs - sum and carry-out. At a primary level, the full adder logic is implemented using XOR, AND and OR gates. However, their extensive use in digital logic makes low-power, highspeed adder cell designs a vast area of study. Improvements are introduced at every level to enhance the performance of the cell. The proposed design in this paper, aims to reduce delay during high speed and low power operation using 28nm technology. The design implements transmission gate structure of MOSFETs resulting in lower leakage power.

The circuit utilizes 16 transistors to realize the full adder. It mainly can be divided into three modules – an 8-transistor complementary XOR/XNOR generator, a 4-transistor transmission gate-based Multiplexer to generate the sum and a pass transistor logic implementation of the carry output. The logic expressions for the adder cell outputs are as follows:

$$Sum = (A \oplus B) \oplus C_{in}$$

$$C_{out} = (A \oplus B) \cdot C_{in} + (A \odot B) \cdot C_{in}$$

The most important part of the circuit is the XOR/XNOR generator module, which performs the XOR and XNOR logic operations on the inputs A and B. Subsequently, the generated complementary outputs are applied to the sum and carry output modules. To enhance the working of the module, a pair of PMOS transistors have been connected in series between the XNOR and supply nodes which reduce the delay and drive a stronger output. By adjusting the aspect ratios of the transistors in the sum module, it can be used to provide minimum gate delay even at a low supply. The carry output module takes both the outputs of the first module and while it can be implemented with two transistors, using an additional pair of complementary

transistors allows for a full level swing at the output. To minimize the channel length, the width can be adjusted to operate in 28nm technology.

II. REFERENCE CIRCUIT

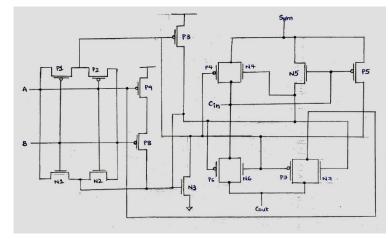


Fig.1. 16T Full Adder Design using Transmission Gate Logic

III. REFERENCE WAVEFORM

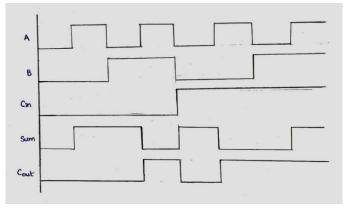


Fig.2. 1-bit Full Adder Input – Output Waveform

IV. REFERENCE PAPERS

- [1] D. K. Jena, R. K. Lal, R. Malik, A. Sen and J. K. Geda, "An improved low power high speed Full Adder design with 28nm for extended region of operation," 2014 International Conference on Electronics, Communication and Computational Engineering (ICECCE), 2014, pp. 137-141.
- [2] C. K. Tung, S. H. Shieh, C. H. Cheng, "Low-powe highspeed full adder for portable electronic application," *Electronics Letters, The Institution of Engineering and Technology*, Vol. 49, No. 17, August 2013.